

Edward T Yu

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217
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236
ext. papers

10,580
ext. citations

4.9
avg, IF

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L-index

#	Paper	IF	Citations
217	Enhanced semiconductor optical absorption via surface plasmon excitation in metal nanoparticles. <i>Applied Physics Letters</i> , 2005 , 86, 063106	3.4	910
216	Improved performance of amorphous silicon solar cells via scattering from surface plasmon polaritons in nearby metallic nanoparticles. <i>Applied Physics Letters</i> , 2006 , 89, 093103	3.4	603
215	Measurement of piezoelectrically induced charge in GaN/AlGaN heterostructure field-effect transistors. <i>Applied Physics Letters</i> , 1997 , 71, 2794-2796	3.4	300
214	A silicon-based photocathode for water reduction with an epitaxial SrTiO ₃ protection layer and a nanostructured catalyst. <i>Nature Nanotechnology</i> , 2015 , 10, 84-90	28.7	292
213	Photocurrent spectroscopy of optical absorption enhancement in silicon photodiodes via scattering from surface plasmon polaritons in gold nanoparticles. <i>Journal of Applied Physics</i> , 2007 , 101, 104309	2.5	291
212	High electron mobility InAs nanowire field-effect transistors. <i>Small</i> , 2007 , 3, 326-32	11	268
211	Analysis of leakage current mechanisms in Schottky contacts to GaN and Al _{0.25} Ga _{0.75} N/GaN grown by molecular-beam epitaxy. <i>Journal of Applied Physics</i> , 2006 , 99, 023703	2.5	227
210	Piezoelectric charge densities in AlGaN/GaN HFETs. <i>Electronics Letters</i> , 1997 , 33, 1230	1.1	226
209	Analysis of reverse-bias leakage current mechanisms in GaN grown by molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2004 , 84, 535-537	3.4	225
208	Metal and dielectric nanoparticle scattering for improved optical absorption in photovoltaic devices. <i>Applied Physics Letters</i> , 2008 , 93, 113108	3.4	199
207	Correlated scanning Kelvin probe and conductive atomic force microscopy studies of dislocations in gallium nitride. <i>Journal of Applied Physics</i> , 2003 , 94, 1448-1453	2.5	170
206	Gate leakage current mechanisms in AlGaN/GaN heterostructure field-effect transistors. <i>Journal of Applied Physics</i> , 2000 , 88, 5951-5958	2.5	158
205	InP nanowire/polymer hybrid photodiode. <i>Nano Letters</i> , 2008 , 8, 775-9	11.5	157
204	Spontaneous and piezoelectric polarization effects in III ^V nitride heterostructures. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1999 , 17, 1742		157
203	III-V nanowire growth mechanism: V/III ratio and temperature effects. <i>Nano Letters</i> , 2007 , 7, 2486-90	11.5	156
202	Precise semiconductor nanowire placement through dielectrophoresis. <i>Nano Letters</i> , 2009 , 9, 2260-6	11.5	154
201	Multiband treatment of quantum transport in interband tunnel devices. <i>Physical Review B</i> , 1992 , 45, 3583-3592	3.3	153

200	Schottky barrier engineering in III \bar{V} nitrides via the piezoelectric effect. <i>Applied Physics Letters</i> , 1998 , 73, 1880-1882	3.4	120
199	Nanoparticle-induced light scattering for improved performance of quantum-well solar cells. <i>Applied Physics Letters</i> , 2008 , 93, 091107	3.4	116
198	Measurement of polarization charge and conduction-band offset at In \bar{x} Ga $\bar{1-x}$ N/GaN heterojunction interfaces. <i>Applied Physics Letters</i> , 2004 , 84, 4644-4646	3.4	116
197	Critical dimensions in coherently strained coaxial nanowire heterostructures. <i>Journal of Applied Physics</i> , 2006 , 99, 114308	2.5	111
196	Deep level defects in n-type GaN grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 1998 , 72, 1211-1213	3.4	106
195	Charge storage in Co nanoclusters embedded in SiO $\bar{2}$ by scanning force microscopy. <i>Applied Physics Letters</i> , 1999 , 74, 472-474	3.4	102
194	Highly controllable and stable quantized conductance and resistive switching mechanism in single-crystal TiO $\bar{2}$ resistive memory on silicon. <i>Nano Letters</i> , 2014 , 14, 4360-7	11.5	101
193	Influence of surface states on the extraction of transport parameters from InAs nanowire field effect transistors. <i>Applied Physics Letters</i> , 2007 , 90, 162112	3.4	101
192	Trap characterization by gate-drain conductance and capacitance dispersion studies of an AlGa \bar{N} /Ga \bar{N} heterostructure field-effect transistor. <i>Journal of Applied Physics</i> , 2000 , 87, 8070-8073	2.5	99
191	Design of Tunneling Field-Effect Transistors Based on Staggered Heterojunctions for Ultralow-Power Applications. <i>IEEE Electron Device Letters</i> , 2010 , 31, 431-433	4.4	94
190	Integrated one diode-one resistor architecture in nanopillar SiO \bar{x} resistive switching memory by nanosphere lithography. <i>Nano Letters</i> , 2014 , 14, 813-8	11.5	85
189	Reduction of reverse-bias leakage current in Schottky diodes on Ga \bar{N} grown by molecular-beam epitaxy using surface modification with an atomic force microscope. <i>Journal of Applied Physics</i> , 2002 , 91, 9821	2.5	85
188	Measurement of drift mobility in AlGa \bar{N} /Ga \bar{N} heterostructure field-effect transistor. <i>Applied Physics Letters</i> , 1999 , 74, 3890-3892	3.4	83
187	Structural and Room-Temperature Transport Properties of Zinc Blende and Wurtzite InAs Nanowires. <i>Advanced Functional Materials</i> , 2009 , 19, 2102-2108	15.6	82
186	Band Offsets in Semiconductor Heterojunctions. <i>Solid State Physics</i> , 1992 , 1-146	2	82
185	Cross-sectional imaging and spectroscopy of GaAs doping superlattices by scanning tunneling microscopy. <i>Applied Physics Letters</i> , 1992 , 61, 795-797	3.4	79
184	Direct observation of ballistic and drift carrier transport regimes in InAs nanowires. <i>Applied Physics Letters</i> , 2006 , 89, 053113	3.4	77
183	Out-of-Plane Electromechanical Response of Monolayer Molybdenum Disulfide Measured by Piezoresponse Force Microscopy. <i>Nano Letters</i> , 2017 , 17, 5464-5471	11.5	71

182	Surface diffusion and substrate-nanowire adatom exchange in InAs nanowire growth. <i>Nano Letters</i> , 2009 , 9, 1967-72	11.5	70
181	Persistent photoconductivity and defect levels in n-type AlGa _{1-x} N/GaN heterostructures. <i>Applied Physics Letters</i> , 1998 , 72, 2745-2747	3.4	69
180	Transport properties of InAs nanowire field effect transistors: The effects of surface states. <i>Journal of Vacuum Science & Technology B</i> , 2007 , 25, 1432		67
179	Interface Adhesion between 2D Materials and Elastomers Measured by Buckle Delaminations. <i>Advanced Materials Interfaces</i> , 2015 , 2, 1500176	4.6	66
178	Photon management for photovoltaics. <i>MRS Bulletin</i> , 2011 , 36, 424-428	3.2	61
177	Scanning tunneling spectroscopy and Kelvin probe force microscopy investigation of Fermi energy level pinning mechanism on InAs and InGaAs clean surfaces. <i>Journal of Applied Physics</i> , 2010 , 108, 023711-5	7.5	60
176	Transport coefficients of InAs nanowires as a function of diameter. <i>Small</i> , 2009 , 5, 77-81	11	60
175	Lateral variations in threshold voltage of an Al _x Ga _{1-x} N/GaN heterostructure field-effect transistor measured by scanning capacitance spectroscopy. <i>Applied Physics Letters</i> , 2001 , 78, 88-90	3.4	57
174	Cross-Sectional Scanning Tunneling Microscopy of Semiconductor Heterostructures. <i>MRS Bulletin</i> , 1997 , 22, 22-26	3.2	53
173	n-CdSe/p-ZnTe based wide band-gap light emitters: Numerical simulation and design. <i>Journal of Applied Physics</i> , 1993 , 73, 4660-4668	2.5	53
172	Epitaxial c-axis oriented BaTiO ₃ thin films on SrTiO ₃ -buffered Si(001) by atomic layer deposition. <i>Applied Physics Letters</i> , 2014 , 104, 082910	3.4	51
171	Piezoelectric polarization associated with dislocations in wurtzite GaN. <i>Applied Physics Letters</i> , 1999 , 74, 573-575	3.4	51
170	Localized dielectric breakdown and antireflection coating in metal-oxide-semiconductor photoelectrodes. <i>Nature Materials</i> , 2017 , 16, 127-131	27	50
169	Measurement of the valence-band offset in strained Si/Ge (100) heterojunctions by x-ray photoelectron spectroscopy. <i>Applied Physics Letters</i> , 1990 , 56, 569-571	3.4	48
168	Influence of surface processing and passivation on carrier concentrations and transport properties in AlGa _{1-x} N/GaN heterostructures. <i>Journal of Applied Physics</i> , 2001 , 90, 1357-1361	2.5	47
167	Reverse-bias leakage current reduction in GaN Schottky diodes by electrochemical surface treatment. <i>Applied Physics Letters</i> , 2003 , 82, 1293-1295	3.4	46
166	Calculation of critical dimensions for wurtzite and cubic zinc blende coaxial nanowire heterostructures. <i>Journal of Vacuum Science & Technology B</i> , 2006 , 24, 2053		42
165	X-ray photoelectron spectroscopy measurement of valence-band offsets for Mg-based semiconductor compounds. <i>Applied Physics Letters</i> , 1994 , 64, 3455-3457	3.4	42

164	Optimization of PbI ₂ /MAPbI ₃ Perovskite Composites by Scanning Electrochemical Microscopy. <i>Journal of Physical Chemistry C</i> , 2016 , 120, 19890-19895	3.8	42
163	A Liquid Junction Photoelectrochemical Solar Cell Based on p-Type MeNH ₃ PbI ₃ Perovskite with 1.05 V Open-Circuit Photovoltage. <i>Journal of the American Chemical Society</i> , 2015 , 137, 14758-64	16.4	41
162	Anisotropy and growth-sequence dependence of atomic-scale interface structure in InAs/Ga _{1-x} In _x Sb superlattices. <i>Applied Physics Letters</i> , 1997 , 70, 75-77	3.4	41
161	Hole tunneling times in GaAs/AlAs double-barrier structures. <i>Applied Physics Letters</i> , 1989 , 55, 744-746	3.4	41
160	Electrical profiling of Si(001) p-n junctions by scanning tunneling microscopy. <i>Applied Physics Letters</i> , 1992 , 61, 201-203	3.4	40
159	Toward Cost-Effective Manufacturing of Silicon Solar Cells: Electrodeposition of High-Quality Si Films in a CaCl ₂ -based Molten Salt. <i>Angewandte Chemie - International Edition</i> , 2017 , 56, 15078-15082	16.4	39
158	Electrochemical Formation of a p-n Junction on Thin Film Silicon Deposited in Molten Salt. <i>Journal of the American Chemical Society</i> , 2017 , 139, 16060-16063	16.4	39
157	Atomic layer deposition of crystalline SrHfO ₃ directly on Ge (001) for high-k dielectric applications. <i>Journal of Applied Physics</i> , 2015 , 117, 054101	2.5	39
156	A Chemical Route to Monolithic Integration of Crystalline Oxides on Semiconductors. <i>Advanced Materials Interfaces</i> , 2014 , 1, 1400081	4.6	38
155	Scanning Kelvin probe microscopy of surface electronic structure in GaN grown by hydride vapor phase epitaxy. <i>Journal of Applied Physics</i> , 2002 , 91, 9924	2.5	38
154	Direct measurement of the polarization charge in AlGa _x N/GaN heterostructures using capacitance-voltage carrier profiling. <i>Applied Physics Letters</i> , 2002 , 80, 3551-3553	3.4	38
153	Large peak current densities in novel resonant interband tunneling heterostructures. <i>Applied Physics Letters</i> , 1990 , 57, 1257-1259	3.4	38
152	Modeling of novel heterojunction tunnel structures. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1990 , 8, 810		38
151	Experimental realization and modeling of a subwavelength frequency-selective plasmonic metasurface. <i>Applied Physics Letters</i> , 2011 , 99, 221106	3.4	37
150	Role of heavy-hole states in interband tunnel structures. <i>Applied Physics Letters</i> , 1991 , 58, 292-294	3.4	37
149	Measurement of the CdSe/ZnTe valence band offset by x-ray photoelectron spectroscopy. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1991 , 9, 2233		37
148	Origin and microscopic mechanism for suppression of leakage currents in Schottky contacts to GaN grown by molecular-beam epitaxy. <i>Journal of Applied Physics</i> , 2003 , 94, 7611	2.5	36
147	Cross-Sectional Scanning Tunneling Microscopy. <i>Chemical Reviews</i> , 1997 , 97, 1017-1044	68.1	35

146	Growth of InAs Nanowires on SiO ₂ Substrates: Nucleation, Evolution, and the Role of Au Nanoparticles. <i>Journal of Physical Chemistry C</i> , 2007 , 111, 13331-13336	3.8	35
145	Experimental observation of negative differential resistance from an InAs/GaSb interface. <i>Applied Physics Letters</i> , 1990 , 57, 683-685	3.4	35
144	Optimization of Lead-free Organic-Inorganic Tin(II) Halide Perovskite Semiconductors by Scanning Electrochemical Microscopy. <i>Electrochimica Acta</i> , 2016 , 220, 205-210	6.7	34
143	Low defect-mediated reverse-bias leakage in (0001) GaN via high-temperature molecular beam epitaxy. <i>Applied Physics Letters</i> , 2010 , 96, 102111	3.4	34
142	Fabrication and characterisation of enhanced barrier AlGaIn/GaN HFET. <i>Electronics Letters</i> , 1999 , 35, 602-604	1.1	34
141	Measurement of the valence band offset in novel heterojunction systems: Si/Ge (100) and AlSb/ZnTe (100). <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1990 , 8, 908		34
140	Improved Performance of Zinc Oxide Thin Film Transistor Pressure Sensors and a Demonstration of a Commercial Chip Compatibility with the New Force Sensing Technology. <i>Advanced Materials Technologies</i> , 2018 , 3, 1700279	6.8	33
139	Light trapping in thin-film solar cells via scattering by nanostructured antireflection coatings. <i>Journal of Applied Physics</i> , 2013 , 114, 044310	2.5	33
138	Enhancement of base conductivity via the piezoelectric effect in AlGaIn/GaN HBTs. <i>Solid-State Electronics</i> , 2000 , 44, 211-219	1.7	32
137	Electrodeposition of crystalline silicon films from silicon dioxide for low-cost photovoltaic applications. <i>Nature Communications</i> , 2019 , 10, 5772	17.4	32
136	Field dependent transport properties in InAs nanowire field effect transistors. <i>Nano Letters</i> , 2008 , 8, 3114-9	11.5	30
135	Excess indium and substrate effects on the growth of InAs nanowires. <i>Small</i> , 2007 , 3, 1683-7	11	30
134	High ON/OFF Ratio and Quantized Conductance in Resistive Switching of TiO_2 on Silicon. <i>IEEE Electron Device Letters</i> , 2013 , 34, 1385-1387	4.4	29
133	Demonstration of resonant transmission in InAs/GaSb/InAs interband tunneling devices. <i>Applied Physics Letters</i> , 1990 , 57, 2675-2677	3.4	29
132	Oxygen-induced bi-modal failure phenomenon in SiO _x -based resistive switching memory. <i>Applied Physics Letters</i> , 2013 , 103, 033521	3.4	28
131	Plasmonic nanoparticle scattering for enhanced performance of photovoltaic and photodetector devices 2008 ,		28
130	Two-dimensional profiling of shallow junctions in Si metal-oxide-semiconductor structures using scanning tunneling spectroscopy and transmission electron microscopy. <i>Journal of Applied Physics</i> , 1996 , 79, 2115-2121	2.5	27
129	Investigation of edge- and bulk-related resistive switching behaviors and backward-scan effects in SiO _x -based resistive switching memory. <i>Applied Physics Letters</i> , 2013 , 103, 193508	3.4	25

128	Band offsets in Si/Si _{1-x} GexCy heterojunctions measured by admittance spectroscopy. <i>Applied Physics Letters</i> , 1997 , 70, 3413-3415	3.4	24
127	Characterization of AlxGa1-xAs/GaAs heterojunction bipolar transistor structures using cross-sectional scanning force microscopy. <i>Journal of Applied Physics</i> , 2000 , 87, 1937-1942	2.5	24
126	Nanoscale characterization of semiconductor materials and devices using scanning probe techniques. <i>Materials Science and Engineering Reports</i> , 1996 , 17, 147-206	30.9	24
125	. <i>IEEE Transactions on Electron Devices</i> , 2011 , 58, 4384-4392	2.9	22
124	Correlation between atomic-scale structure and mobility anisotropy in InAs/Ga1-xInxSb superlattices. <i>Physical Review B</i> , 1998 , 57, 6534-6539	3.3	22
123	Scanning tunneling microscopy of InAs/Ga1-xInxSb superlattices. <i>Applied Physics Letters</i> , 1994 , 65, 201-203	3.4	22
122	Asymmetric light reflectance from metal nanoparticle arrays on dielectric surfaces. <i>Scientific Reports</i> , 2015 , 5, 18331	4.9	21
121	Light scattering into silicon-on-insulator waveguide modes by random and periodic gold nanodot arrays. <i>Journal of Applied Physics</i> , 2009 , 105, 073101	2.5	21
120	Scanning capacitance microscopy of AlGaIn/GaN heterostructure field-effect transistor epitaxial layer structures. <i>Applied Physics Letters</i> , 1999 , 75, 2250-2252	3.4	21
119	III-V/II-VI double-barrier resonant tunneling structures. <i>Applied Physics Letters</i> , 1988 , 53, 60-62	3.4	21
118	Flexible, low-loss, large-area, wide-angle, wavelength-selective plasmonic multilayer metasurface. <i>Journal of Applied Physics</i> , 2013 , 114, 133104	2.5	20
117	Electrochemical Monitoring of TiO ₂ Atomic Layer Deposition by Chronoamperometry and Scanning Electrochemical Microscopy. <i>Chemistry of Materials</i> , 2013 , 25, 4165-4172	9.6	20
116	Observation of subsurface monolayer thickness fluctuations in InGaIn/GaN quantum wells by scanning capacitance microscopy and spectroscopy. <i>Applied Physics Letters</i> , 2004 , 85, 407-409	3.4	20
115	Nanoscale current transport in epitaxial SrTiO ₃ on n+-Si investigated with conductive atomic force microscopy. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2004 , 22, 2030		20
114	Local conductivity and surface photovoltage variations due to magnesium segregation in p-type GaN. <i>Journal of Applied Physics</i> , 2004 , 95, 6225-6231	2.5	19
113	Direct measurement and characterization of n+ superhalo implants in a 120 nm gate-length Si metaloxide semiconductor field-effect transistor using cross-sectional scanning capacitance microscopy. <i>Applied Physics Letters</i> , 2002 , 81, 3993-3995	3.4	18
112	Atomic-scale structure of InAs/InAs _{1-x} Sbx superlattices grown by modulated molecular beam epitaxy. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1996 , 14, 2940		17
111	Scanned electrical probe characterization of carrier transport behavior in InAs nanowires. <i>Journal of Vacuum Science & Technology B</i> , 2006 , 24, 2036		16

110	Miscut-angle dependence of perpendicular magnetic anisotropy in thin epitaxial CoPt ₃ films grown on vicinal MgO. <i>Applied Physics Letters</i> , 2002 , 81, 517-519	3.4	16
109	Effect of band mixing on hole-tunneling times in GaAs/AlAs double-barrier heterostructures. <i>Physical Review B</i> , 1992 , 45, 3576-3582	3.3	16
108	Scanning tunneling microscopy and spectroscopy of Si/SiGe(001) superlattices. <i>Applied Physics Letters</i> , 1992 , 61, 3166-3168	3.4	16
107	Integration of vertical InAs nanowire arrays on insulator-on-silicon for electrical isolation. <i>Applied Physics Letters</i> , 2008 , 93, 203109	3.4	15
106	Scanning gate microscopy of InAs nanowires. <i>Applied Physics Letters</i> , 2007 , 90, 233118	3.4	15
105	Zeta Potential Dependent Self-Assembly for Very Large Area Nanosphere Lithography. <i>Nano Letters</i> , 2020 , 20, 5090-5096	11.5	14
104	Commutativity of the GaAs/AlAs(100) band offset. <i>Physical Review B</i> , 1988 , 38, 12764-12767	3.3	14
103	Quantum state engineering with ultra-short-period (AlN) _m /(GaN) _n superlattices for narrowband deep-ultraviolet detection. <i>Nanoscale</i> , 2014 , 6, 14733-9	7.7	13
102	Epitaxy of Al films on GaN studied by reflection high-energy electron diffraction and atomic force microscopy. <i>Applied Physics Letters</i> , 1997 , 70, 990-992	3.4	13
101	Cross-sectional scanning tunneling microscopy of GaAsSb/GaAs quantum well structures. <i>Journal of Applied Physics</i> , 2002 , 92, 3761-3770	2.5	13
100	Charging effects in AlGaIn/GaN heterostructures probed using scanning capacitance microscopy. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2000 , 18, 2304		13
99	Transfer of patterned ion-cut silicon layers. <i>Applied Physics Letters</i> , 1998 , 73, 2772-2774	3.4	13
98	Characterization of arsenide/phosphide heterostructure interfaces grown by gas-source molecular beam epitaxy. <i>Applied Physics Letters</i> , 1995 , 67, 932-934	3.4	13
97	Interfacial reactions and band offsets in the AlSb/GaSb/ZnTe material system. <i>Physical Review B</i> , 1992 , 46, 13379-13388	3.3	13
96	Monolithic integration of perovskites on Ge(001) by atomic layer deposition: a case study with SrHf _x Ti _{1-x} O ₃ . <i>MRS Communications</i> , 2016 , 6, 125-132	2.7	13
95	Ultra-stable 2D layered methylammonium cadmium trihalide perovskite photoelectrodes. <i>Journal of Materials Chemistry C</i> , 2018 , 6, 11552-11560	7.1	13
94	Subwavelength nanostructures integrated with polymer-packaged III-V solar cells for omnidirectional, broad-spectrum improvement of photovoltaic performance. <i>Progress in Photovoltaics: Research and Applications</i> , 2015 , 23, 1398-1405	6.8	12
93	Increased InAs quantum dot size and density using bismuth as a surfactant. <i>Applied Physics Letters</i> , 2014 , 105, 253104	3.4	12

92	Voltage-controlled ferromagnetism and magnetoresistance in LaCoO ₃ /SrTiO ₃ heterostructures. <i>Journal of Applied Physics</i> , 2013 , 114, 183909	2.5	12
91	Large-area omnidirectional antireflection coating on low-index materials. <i>Journal of the Optical Society of America B: Optical Physics</i> , 2013 , 30, 2584	1.7	12
90	Scanning capacitance spectroscopy of an Al _x Ga _{1-x} N/GaN heterostructure field-effect transistor structure: Analysis of probe tip effects. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2002 , 20, 1671		12
89	Structural coloration with hourglass-shaped vertical silicon nanopillar arrays. <i>Optics Express</i> , 2018 , 26, 30952-30968	3.3	12
88	Out-of-plane electromechanical coupling in transition metal dichalcogenides. <i>Applied Physics Letters</i> , 2020 , 116, 053101	3.4	11
87	Wide-angle wavelength-selective multilayer optical metasurfaces robust to interlayer misalignment. <i>Journal of the Optical Society of America B: Optical Physics</i> , 2013 , 30, 27	1.7	11
86	Local electronic properties of AlGa _N /GaN heterostructures probed by scanning capacitance microscopy. <i>Journal of Electronic Materials</i> , 2000 , 29, 274-280	1.9	11
85	A scanning tunneling microscopy study of atomic-scale clustering in InAsP/InP heterostructures. <i>Applied Physics Letters</i> , 1998 , 72, 2135-2137	3.4	11
84	Commutativity of the GaAs/AlAs (100) band offset. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1989 , 7, 391		11
83	Large peak-to-valley current ratios in triple barrier heterostructures. <i>Solid-State Electronics</i> , 1989 , 32, 1095-1099	1.7	11
82	Interface structure in arsenide/phosphide heterostructure grown by gas-source MBE and low-pressure MOVPE. <i>Journal of Electronic Materials</i> , 1997 , 26, 64-69	1.9	10
81	Cross-sectional scanning thermal microscopy of ErAs/GaAs superlattices grown by molecular beam epitaxy. <i>Nanotechnology</i> , 2015 , 26, 265701	3.4	9
80	Crystalline SrZrO ₃ deposition on Ge (001) by atomic layer deposition for high-k dielectric applications. <i>Journal of Applied Physics</i> , 2018 , 124, 044102	2.5	9
79	Improvement of performance of InAs quantum dot solar cell by inserting thin AlAs layers. <i>Nanoscale Research Letters</i> , 2011 , 6, 83	5	9
78	Computational analysis of thin film InGaAs/GaAs quantum well solar cells with back side light trapping structures. <i>Optics Express</i> , 2012 , 20 Suppl 6, A864-78	3.3	9
77	Semiconductor heterostructures and optimization of light-trapping structures for efficient thin-film solar cells. <i>Journal of Optics (United Kingdom)</i> , 2012 , 14, 024007	1.7	9
76	Nanoscale Characterization of Materials. <i>MRS Bulletin</i> , 1997 , 22, 17-21	3.2	9
75	Demonstration and analysis of reduced reverse-bias leakage current via design of nitride semiconductor heterostructures grown by molecular-beam epitaxy. <i>Journal of Applied Physics</i> , 2006 , 99, 014501	2.5	9

74	Characterization of CdSe/ZnTe heterojunctions. <i>Journal of Crystal Growth</i> , 1991 , 111, 820-822	1.6	9
73	Localized variations in electronic structure of AlGa _{1-x} N/GaN heterostructures grown by molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2001 , 79, 2749-2751	3.4	8
72	Polarization charges and polarization-induced barriers in Al _x Ga _{1-x} N/GaN and In _y Ga _{1-y} N/GaN heterostructures. <i>Applied Physics Letters</i> , 2001 , 79, 2916-2918	3.4	8
71	Negative differential resistance due to resonant interband tunneling of holes. <i>Journal of Applied Physics</i> , 1990 , 68, 3744-3746	2.5	8
70	Effect of particle size distribution on near-field thermal energy transfer within the nanoparticle packings. <i>Journal of Photonics for Energy</i> , 2019 , 9, 1	1.2	8
69	A Low-Leakage Epitaxial High- κ Gate Oxide for Germanium Metal-Oxide-Semiconductor Devices. <i>ACS Applied Materials & Interfaces</i> , 2016 , 8, 5416-23	9.5	7
68	Toward Cost-Effective Manufacturing of Silicon Solar Cells: Electrodeposition of High-Quality Si Films in a CaCl ₂ -based Molten Salt. <i>Angewandte Chemie</i> , 2017 , 129, 15274-15278	3.6	7
67	Fabrication of birefringent nanocylinders for single-molecule force and torque measurement. <i>Nanotechnology</i> , 2014 , 25, 235304	3.4	7
66	Quantitative scanning thermal microscopy of ErAs/GaAs superlattice structures grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2013 , 102, 061912	3.4	7
65	Measurement of band offsets in Si/Si _{1-x} G _x and Si/Si _{1-x} G _x Cy heterojunctions. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1997 , 15, 1108		7
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